Application No.: 09/926,791

Art Unit: 2818

Examiner: Michael T. TRAN

## **LIST OF CURRENT CLAIMS**

1. (Currently Amended) A semiconductor memory chip module comprising:

a first memory chip (4) of a first type;

a second memory chip <del>(6)</del> of a second type different from the first type of

memory chip,; and

an electric connection (14, 16) between the first and second memory chips (4,

<del>6),</del>;

wherein the memory chips (4, 6) are disposed one above the other in different

levels and connected by vertical chip interconnections;

wherein memory cells of the first memory chip are firmly allocated to certain

memory cells of the second memory chip, and the mutually allocated memory cells are

directly interconnected electrically.

2. (Canceled)

3. (Previously Amended) A chip module according to claim 1, wherein the first

type corresponds to a nonvolatile memory, for example EEPROM, and the second type

to a volatile memory, for example SRAM.

4. (Currently amended) A chip module according to claim 1, wherein at least

one further chip (8, 16) is provided in a further level.

5. (Currently amended) A chip module according to claim 4, wherein the further

chip contains decoder circuits (10, 12) for the memory chips (4, 6).

6. (Previously amended) A chip module according to claim 1, wherein an energy

buffer is formed in at least one of the levels.

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7. (Currently amended) A chip module according to claim 6, wherein the energy buffer is formed as an integrated buffer capacitor (20).

- 8. (Previously amended) A chip module according to claim 1, formed for a smart card.
- 9. (Previously amended) A smart card having a semiconductor memory chip module according to claim 1.